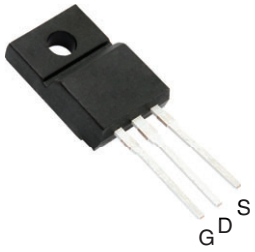
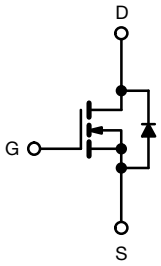
Power MOSFET

TO-220 FULLPAK





N-Channel MOSFET

FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT

APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptible power supply
- High speed power switching
- High voltage isolation = 2.5 kV_{RMS} (t = 60 s, f = 60 Hz)

TYPICAL SMPS TOPOLOGIES

- Single transistor forward
- Active clamped forward

PRODUCT SUMMARY		
V_{DS} (V)	600	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	0.75
Q_g max. (nC)	49	
Q_{gs} (nC)	13	
Q_{gd} (nC)	20	
Configuration	Single	

ORDERING INFORMATION	
Package	TO-220 FULLPAK
Lead (Pb)-free	IRFIB6N60APbF

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	600	V
Gate-source voltage			V_{GS}	± 30	
Continuous drain current	V_{GS} at 10 V	T_C = 25 °C	I_D	5.5	
		T_C = 100 °C		3.5	
Pulsed drain current [a]			I_{DM}	37	
Linear derating factor				0.48	W/°C
Single pulse avalanche energy [b]			E_{AS}	290	mJ
Repetitive avalanche current [a]			I_{AR}	9.2	A
Repetitive avalanche energy [a]			E_{AR}	6.0	mJ
Maximum power dissipation	T_C = 25 °C		P_D	60	W
Peak diode recovery dV/dt [c]			dV/dt	5.0	V/ns
Operating junction and storage temperature range			T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) [d]	For 10 s			300	
Mounting torque	M3 screw			0.6	Nm

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. Starting T_J = 25 °C, L = 6.8 mH, R_G = 25 Ω, I_{AS} = 9.2 A (see fig. 12)
c. $I_{SD} \leq 9.2$ A, dI/dt ≤ 50 A/μs, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C
d. 1.6 mm from case

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THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	65	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	2.1	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-ssource breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		600	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA [d]		-	660	-	mV/°C
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2.0	-	4.0	V
Gate-source leakage	I_{GSS}	V_{GS} = ± 30 V		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 600 V, V_{GS} = 0 V		-	-	25	µA
		V_{DS} = 480 V, V_{GS} = 0 V, T_J = 125 °C		-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 3.3 A [b]	-	-	0.75	Ω
Forward transconductance	g_{fs}	V_{DS} = 25 V, I_D = 5.5 A		5.5	-	-	S
Dynamic							
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	1400	-	pF
Output capacitance	C_{oss}			-	180	-	
Reverse transfer capacitance	C_{rss}			-	7.1	-	
Output capacitance	C_{oss}	V_{GS} = 0 V	V_{DS} = 1.0 V, f = 1.0 MHz	-	1957	-	
			V_{DS} = 480 V, f = 1.0 MHz	-	49	-	
Effective output capacitance	C_{oss} eff.		V_{DS} = 0 V to 480 V [c]	-	96	-	
Total gate charge	Q_g	V_{GS} = 10 V	I_D = 9.2 A, V_{DS} = 400 V, see fig. 6 and 13 [b]	-	-	49	nC
Gate-source charge	Q_{gs}			-	-	13	
Gate-drain charge	Q_{gd}			-	-	20	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 300 V, I_D = 9.2 A, R_G = 9.1 Ω, R_D = 35.5 Ω, see fig. 10 [b]		-	13	-	ns
Rise time	t_r			-	25	-	
Turn-off delay time	$t_{d(off)}$			-	30	-	
Fall time	t_f			-	22	-	
Gate input resistance	R_g	f = 1 MHz, open drain		0.5	-	3.2	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	5.5	A
Pulsed diode forward current [a]	I_{SM}			-	-	37	
Body diode voltage	V_{SD}	T_J = 25 °C, I_S = 9.2 A, V_{GS} = 0 V [b]		-	-	1.5	V
Body diode reverse recovery time	t_{rr}	T_J = 25 °C, I_F = 9.2 A, dI/dt = 100 A/µs [b]		-	530	800	ns
Body diode reverse recovery charge	Q_{rr}			-	3.0	4.4	µC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %
c. C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}
d. t = 60 s, f = 60 Hz

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

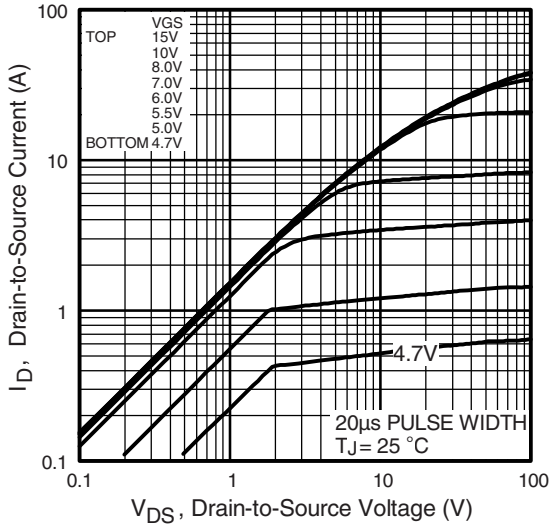


Fig. 1 - Typical Output Characteristics

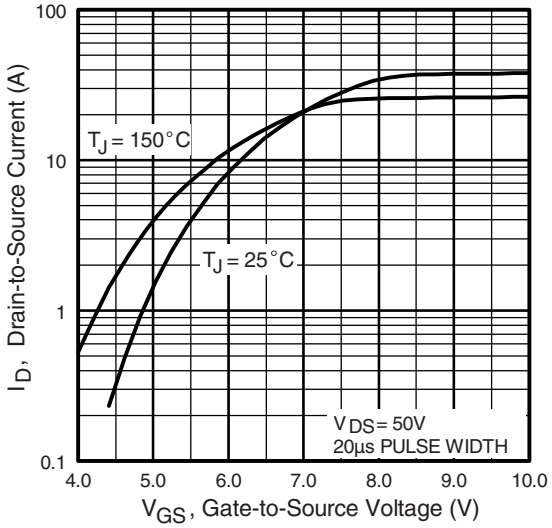


Fig. 3 - Typical Transfer Characteristics

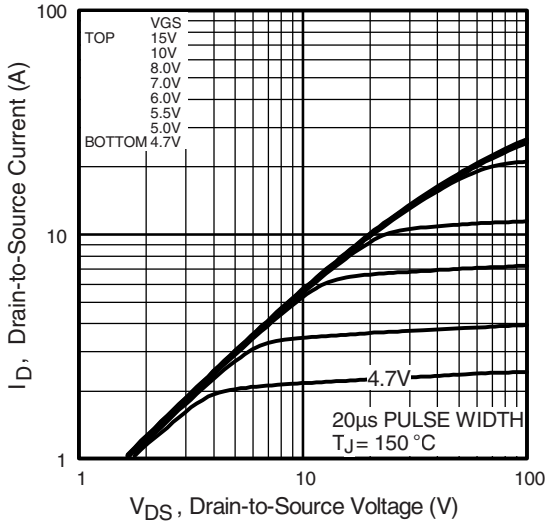


Fig. 2 - Typical Output Characteristics

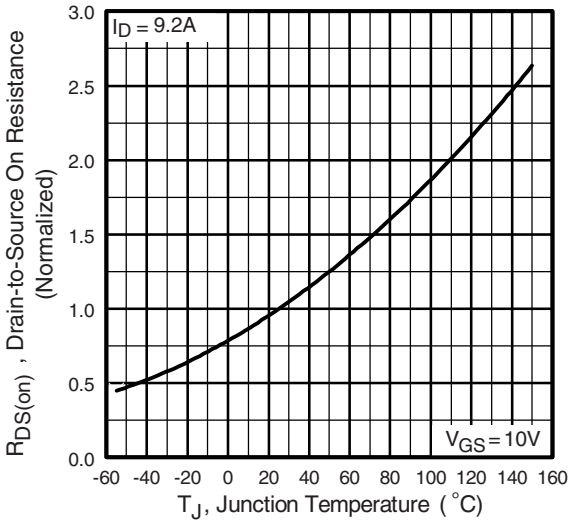


Fig. 4 - Normalized On-Resistance vs. Temperature

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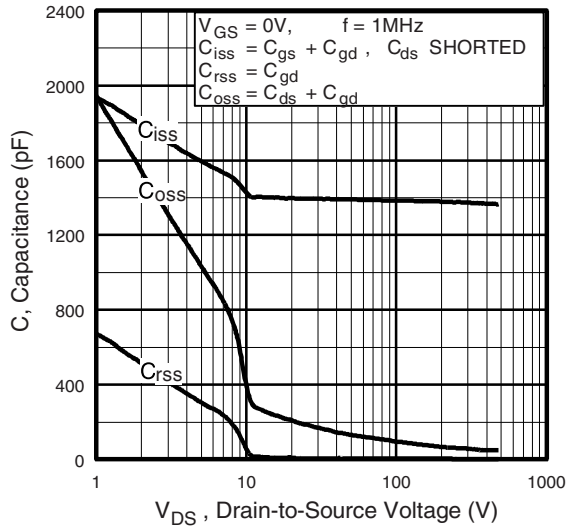


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

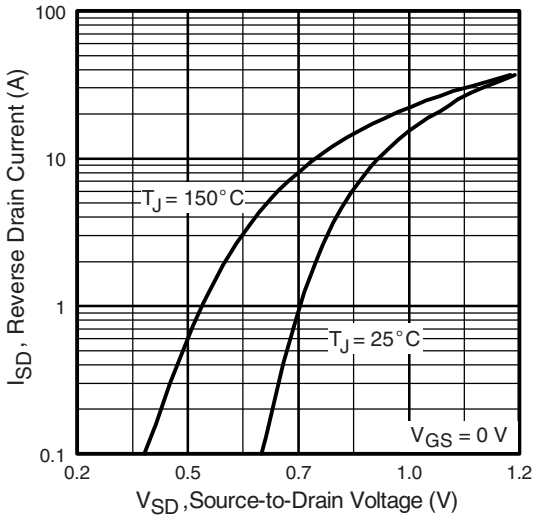


Fig. 7 - Typical Source-Drain Diode Forward Voltage

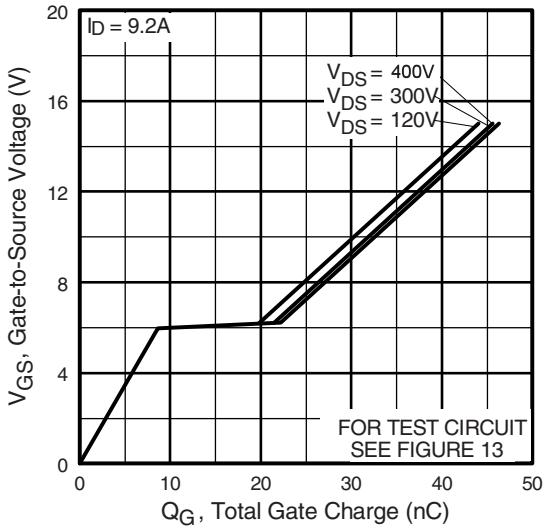


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

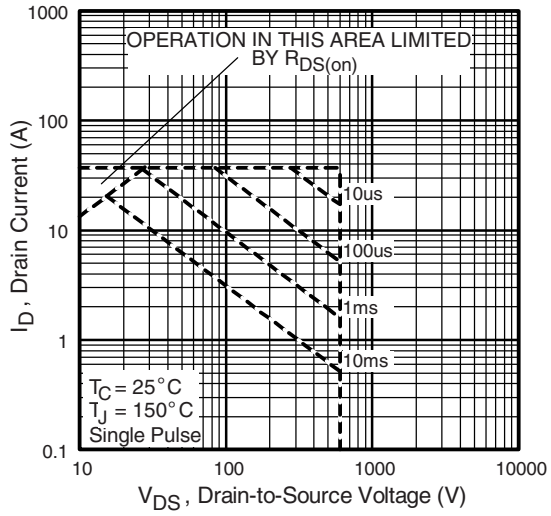


Fig. 8 - Maximum Safe Operating Area

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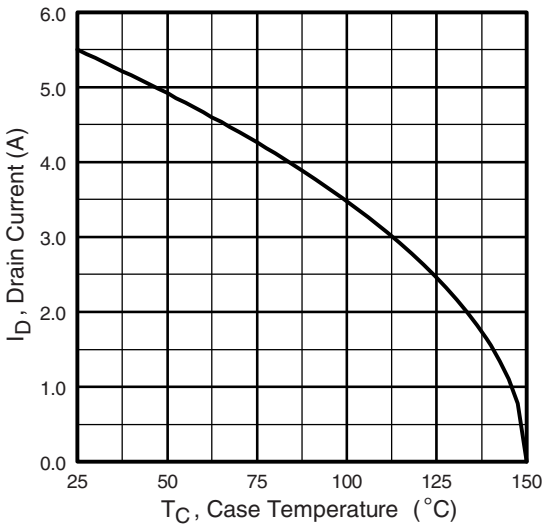


Fig. 9 - Maximum Drain Current vs. Case Temperature

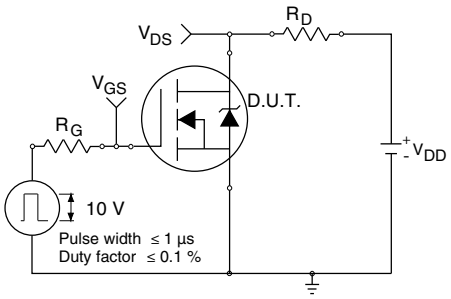


Fig. 10a - Switching Time Test Circuit

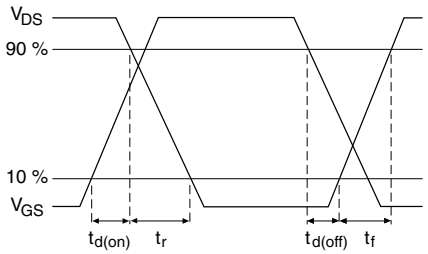


Fig. 10b - Switching Time Waveforms

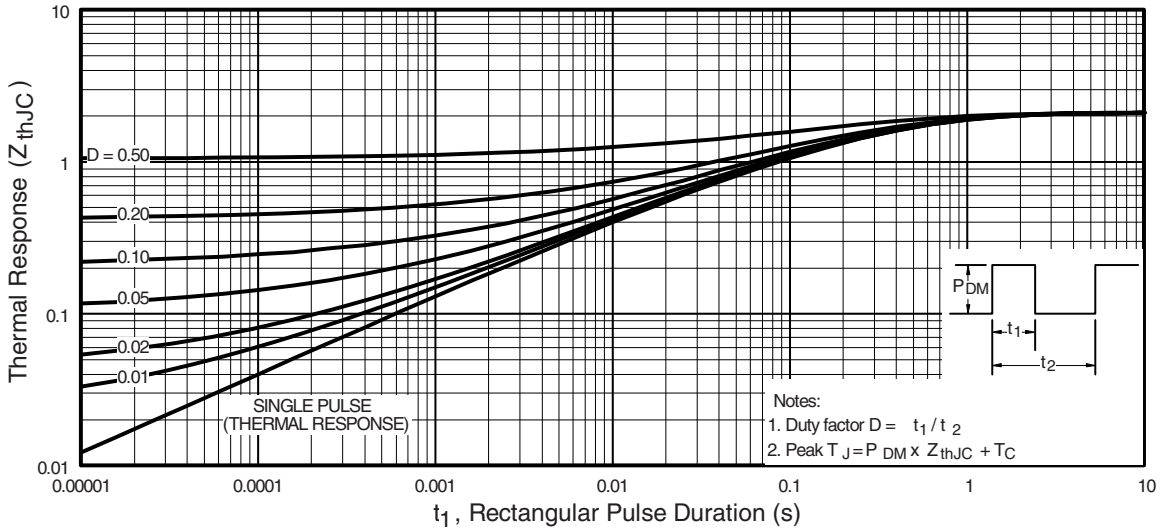


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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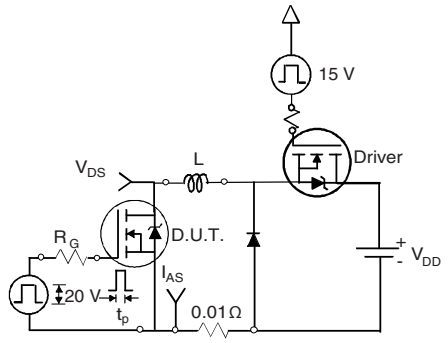


Fig. 12a - Unclamped Inductive Test Circuit

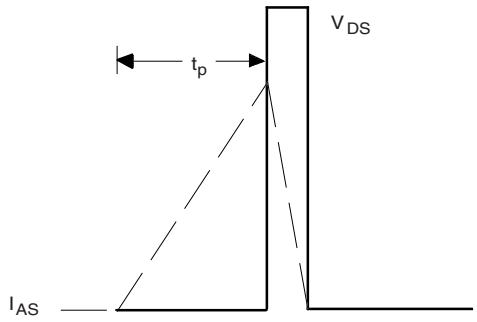


Fig. 12b - Unclamped Inductive Waveforms

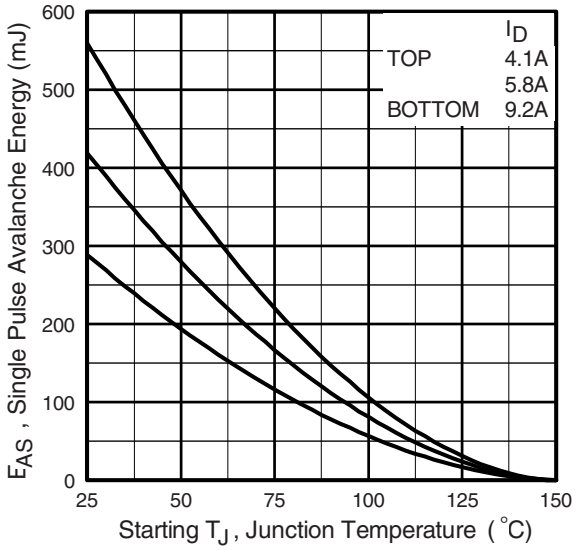


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

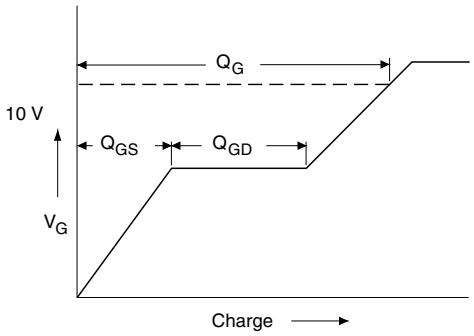


Fig. 13a - Basic Gate Charge Waveform

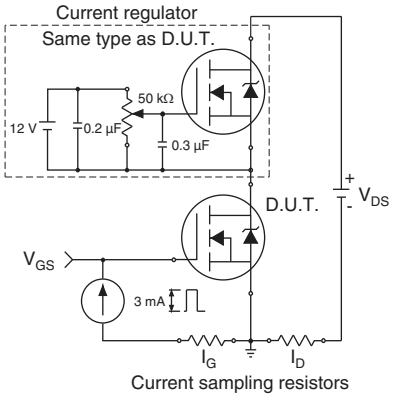
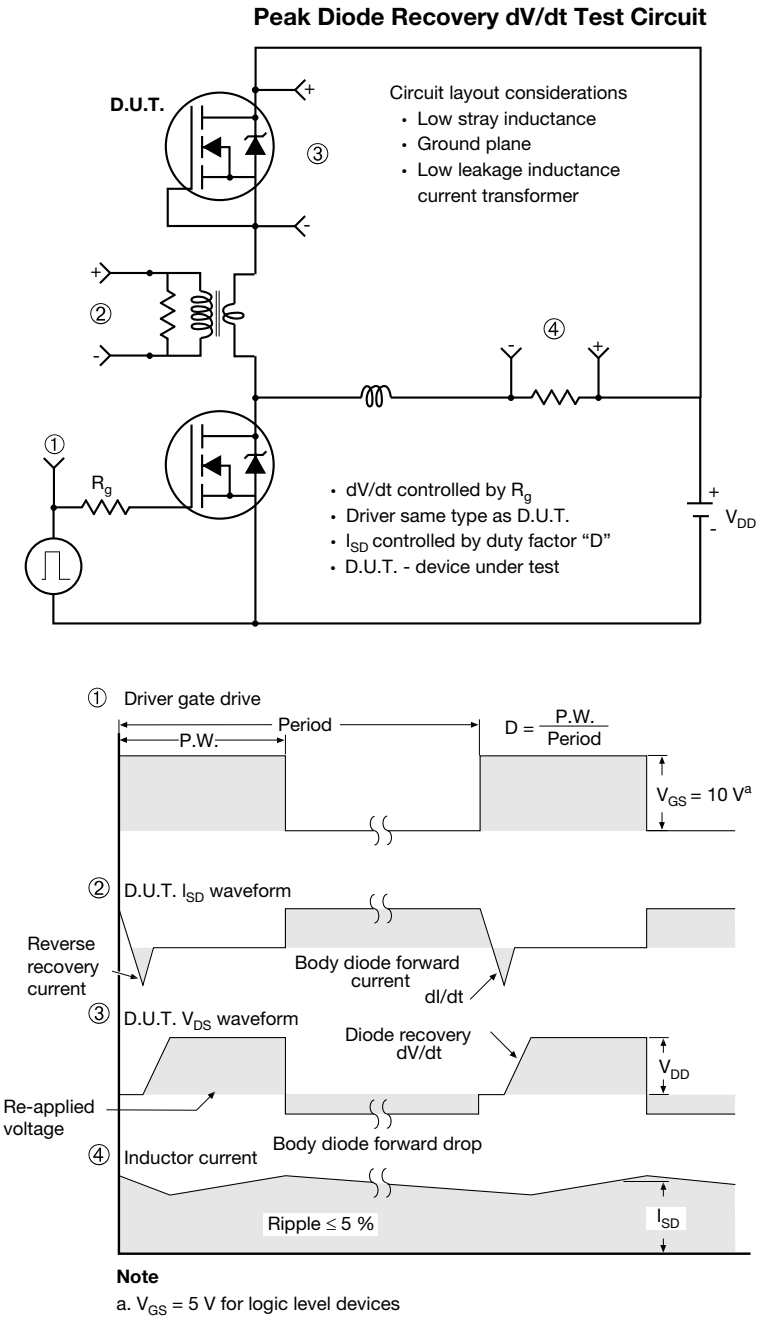


Fig. 13b - Gate Charge Test Circuit

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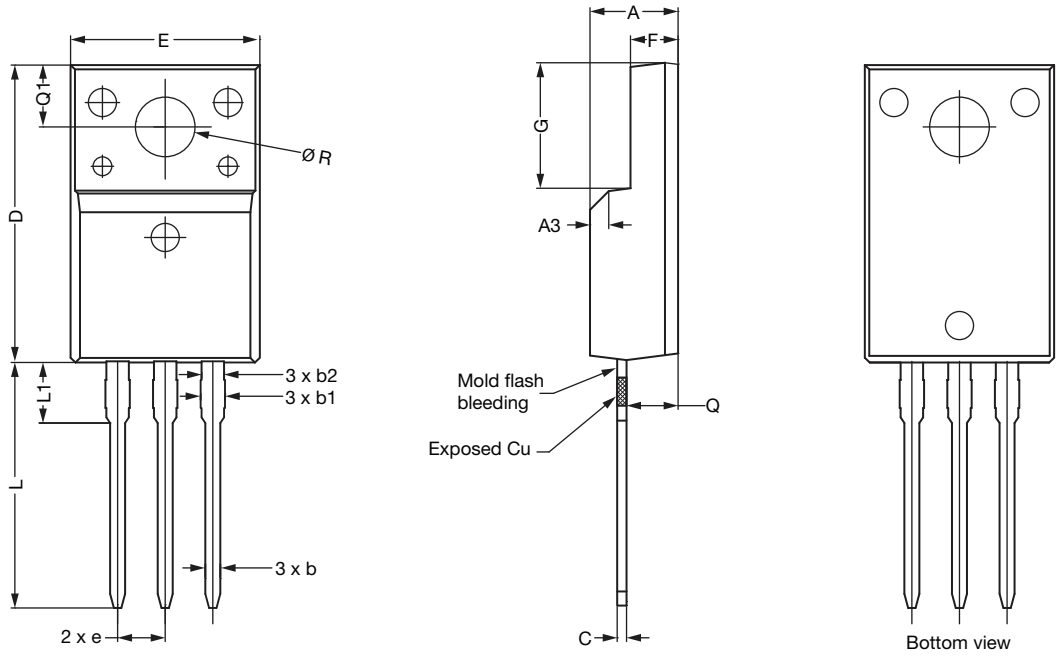
a. V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel

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TO-220 FULLPAK (High Voltage)

OPTION 1: FACILITY CODE = 9



	MILLIMETERS		
DIM.	**MIN.**	**NOM.**	**MAX.**
A	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
C	0.45	0.50	0.63
D	15.80	15.87	15.97
e		2.54 BSC	
E	10.00	10.10	10.30
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
Ø R	3.08	3.18	3.28

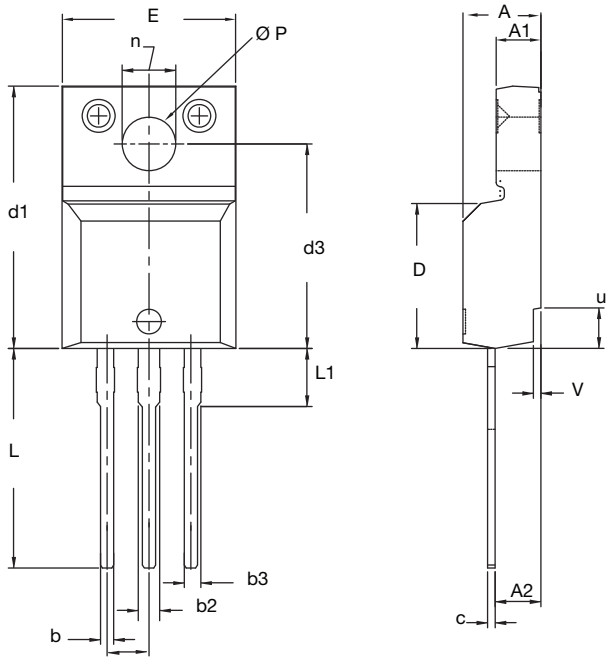
Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking

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OPTION 2: FACILITY CODE = Y



	MILLIMETERS		INCHES	
DIM.	**MIN.**	**MAX.**	**MIN.**	**MAX.**
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
V	0.400	0.500	0.016	0.020
ECN: E19-0180-Rev. D, 08-Apr-2019 DWG: 5972				

Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
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Üreticileri görün

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Teklif isteyin

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